BFP196WN

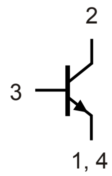
Low noise silicon bipolar RF transistor

Product description

- NPN silicon planar epitaxial transistor in 4-pin dual-emitter SOT343 package for low noise and low distortion wideband amplifiers. This RF transistor benefits from Infineon long-term experience in RF components and combines ease-of-use to stable volumes production, at benchmark quality and reliability.

Features

- For high voltage applications V_{CE} < 12 V
- Maximal power P_{tot} = 700 mW
- Transition frequency f_T = 7.5 GHz
- Noise figure NF_{min} = 1.3 dB at 900 MHz
- Easy to use Pb-free (RoHS compliant) and halogen-free industry standard SOT343 package with visible leads



Application

- GNSS active antenna
- Amplifiers in antenna and telecommunications systems
- CATV
- Power amplifier for DECT and PCN systems

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Device information

Attention: ***ESD (Electrostatic discharge) sensitive device, observe handling precautions***

Type / Ordering code	Package	Pin configuration				Marking	Related Links
BFP196WN / BFP196WNH6327XTSA1	SOT343	1=E	2=C	3=B	4=E	RLs	see ***SOT343 Package***

Table of contents

Product description . . . 1
Features . . . 1
Application . . . 1
Product validation . . . 1
Device information . . . 1
Table of contents . . . 2
1 Absolute maximum ratings . . . 3
2 Thermal characteristics . . . 4
3 Electrical performance in test fixture . . . 5
3.1 DC parameter table . . . 5
3.2 AC parameter tables . . . 5
3.3 Characteristic DC diagrams . . . 8
3.4 Characteristic AC diagrams . . . 11
4 SOT343 Package . . . 17
Revision history . . . 18
Trademarks . . . 19

1 Absolute maximum ratings

Table 1 Absolute maximum ratings at T_A = 25 °C (unless otherwise specified)

Parameter	Symbol	Values		Unit	Note or Test condition
		Min.	Max.		
Collector emitter voltage	V_{CEO}	–	12	V	Base open
Collector emitter voltage	V_{CES}	–	20	V	Emitter / base short circuited
Collector base voltage	V_{CBO}	–	20	V	Emitter open
Emitter base voltage	V_{EBO}	–	2	V	Collector open
DC collector current	I_C	–	150	mA	–
DC base current	I_B	–	15	mA	–
Total power	P_{tot}	–	700	mW	–
Junction temperature	T_J	–	150	°C	–
Storage temperature	T_{Stg}	-55	150	°C	–

Attention: ***Stresses above the maximum values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings. Exceeding only one of these values may cause irreversible damage to the component.***

2 Thermal characteristics

Table 2 Thermal resistance

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Junction - soldering point	R_{thJS}	–	115	–	K/W	[1]

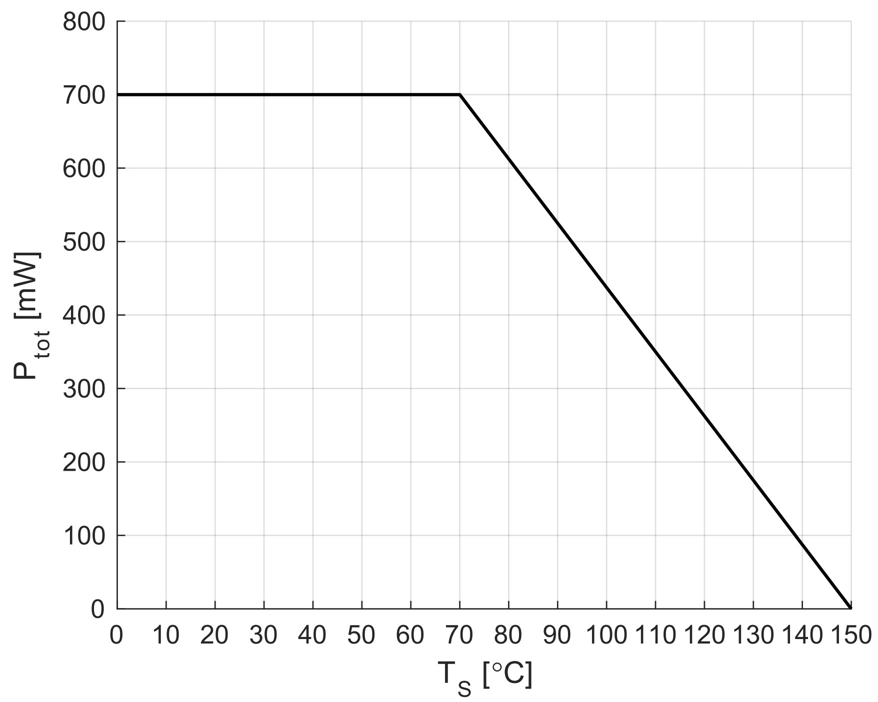


Figure 1 Absolute maximum power dissipation P_{tot} vs. T_s

Note: *In the horizontal part of the above curve the junction temperature T_J is lower than $T_{J,max}$. In the declining slope it is $T_J = T_{J,max}$. P_{tot} has to be reduced according to the curve in order not to exceed $T_{J,max}$. It is $T_{J,max} = T_S + P_{tot} * R_{THJS}$.*

1 For the definition of R_{thJS} please refer to the application note AN077

3 Electrical performance in test fixture

3.1 DC parameter table

Table 3 DC characteristics at T_A = 25 °C

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	V_{CEO}	12	–	–	V	I_C = 1 mA, open base
Collector emitter leakage current	I_{CES}	–	–	100	µA	V_{CE} = 20 V, V_{BE} = 0 V Emitter / base short circuited
Collector base leakage current	I_{CBO}	–	–	100	nA	V_{CB} = 10 V, V_{BE} = 0 Open emitter
Emitter base leakage current	I_{EBO}	–	–	1	µA	V_{EB} = 1 V, I_C = 0 Open collector
DC current gain	h_{FE}	70	100	140		V_{CE} = 8 V, I_C = 50 mA Pulse measured

3.2 AC parameter tables

Table 4 General AC characteristics at T_A = 25 °C

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Transition frequency	f_T	5	7.5	–	GHz	V_{CE} = 8 V, I_C = 90 mA, f=500 MHz
Collector base capacitance	C_{CB}	–	0.9	–	pF	V_{CB} = 10 V, V_{BE} = 0 V, f = 1 MHz Emitter grounded
Collector emitter capacitance	C_{CE}	–	0.35	–	pF	V_{CE} = 10 V, V_{BE} = 0 V, f = 1 MHz Base grounded
Emitter base capacitance	C_{EB}	–	3.8	–	pF	V_{EB} = 0.5 V, V_{CB} = 0 V, f = 1 MHz Collector grounded

Electrical performance in test fixture

Measurement setup for the AC characteristics shown in the following tables is a test fixture with Bias T's in a 50 Ω system, T_A = 25 °C.

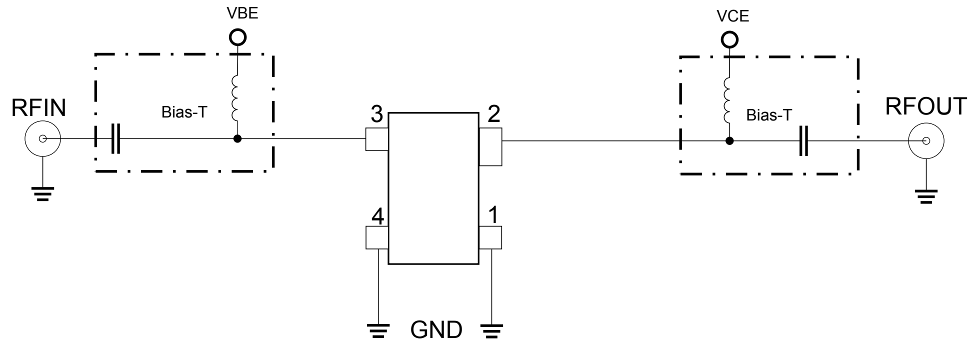


Figure 2 BFP196WN testing circuit

Table 5 AC characteristics, V_{CE} = 8 V, f = 0.45 GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain					dB	I_C = 50 mA
Maximum power gain	G_{ms}	–	23.5	–		$Z_s = Z_{Sopt}$, $Z_L = Z_{Lopt}$
Transducer gain	$\|S_{21}\|^2$	–	19.0	–		Z_S=Z_L=50 Ω
Minimum noise figure	NFmin	–	0.95	–	dB	I_C = 20 mA, $Z_S = Z_{Sopt}$
Linearity					dBm	I_C = 50 mA
1 dB compression point at output	OP1dB	–	19	–		Z_S=Z_L=50 Ω
3rd order intercept point at output	OIP3	–	32	–		

Table 6 AC characteristics, V_{CE} = 8 V, f = 0.9 GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain					dB	I_C = 50 mA
Maximum power gain	G_{ms}	–	17.0	–		$Z_s = Z_{Sopt}$, $Z_L = Z_{Lopt}$
Transducer gain	$\|S_{21}\|^2$	–	13.0	–		Z_S=Z_L=50 Ω
Minimum noise figure	NFmin	–	1.1	–	dB	I_C = 20 mA, $Z_S = Z_{Sopt}$
Linearity					dBm	I_C = 50 mA
1 dB compression point at output	OP1dB	–	19	–		Z_S=Z_L=50 Ω
3rd order intercept point at output	OIP3	–	32	–		

Electrical performance in test fixture

Table 7 AC characteristics, V_{CE} = 8 V, f = 1.5 GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain					dB	I_C = 50 mA
Maximum power gain	G_{ms}	–	12.5	–		$Z_s = Z_{Sopt}$, $Z_L = Z_{Lopt}$
Transducer gain	$\|S_{21}\|^2$	–	8.5	–		Z_S=Z_L=50 Ω
Minimum noise figure	NFmin	–	1.7	–	dB	I_C = 20 mA, $Z_S = Z_{Sopt}$
Linearity					dBm	I_C = 50 mA
1 dB compression point at output	OP1dB	–	19	–		Z_S=Z_L=50 Ω
3rd order intercept point at output	OIP3	–	32	–		

Table 8 AC characteristics, V_{CE} = 8 V, f =1.9 GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain					dB	I_C = 50 mA
Maximum power gain	G_{ms}	–	11	–		$Z_s = Z_{Sopt}$, $Z_L = Z_{Lopt}$
Transducer gain	$\|S_{21}\|^2$	–	6.5	–		Z_S=Z_L=50 Ω
Minimum noise figure	NFmin	–	2.1	–	dB	I_C = 20 mA, $Z_S = Z_{Sopt}$
Linearity					dBm	I_C = 50 mA
1 dB compression point at output	OP1dB	–	19	–		Z_S=Z_L=50 Ω
3rd order intercept point at output	OIP3	–	32	–		

Table 9 AC characteristics, V_{CE} = 5 V, f = 2.4 GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain					dB	
Maximum power gain	G_{ms}	–	9.7	–		I_C = 50 mA
Transducer gain	$\|S_{21}\|^2$	–	4.8	–		$Z_s = Z_{Sopt}$, $Z_L = Z_{Lopt}$
						Z_S=Z_L=50 Ω
Minimum noise figure	NFmin	–	2.5	–	dB	I_C = 20 mA, $Z_S = Z_{Sopt}$
Linearity					dBm	I_C = 50 mA
1 dB compression point at output	OP1dB	–	19	–		Z_S=Z_L=50 Ω
3rd order intercept point at output	OIP3	–	32	–		

3.3 Characteristic DC diagrams

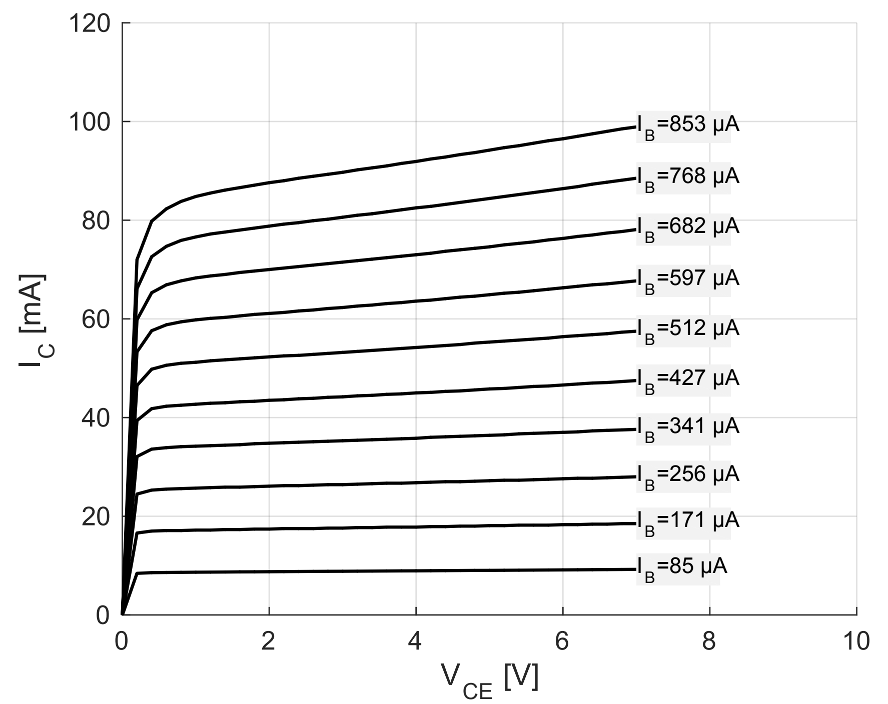


Figure 3 **Collector current $I_C = f(V_{CE})$, I_B = parameter**

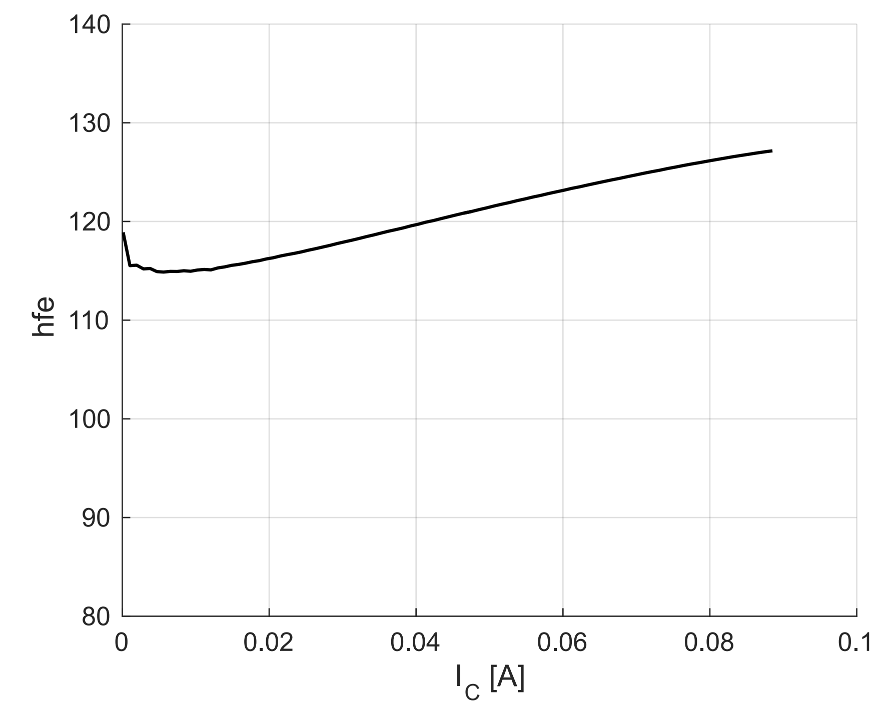


Figure 4 **Current gain $h_{FE} = f(I_C)$, V_{CE} = 8 V**

Electrical performance in test fixture

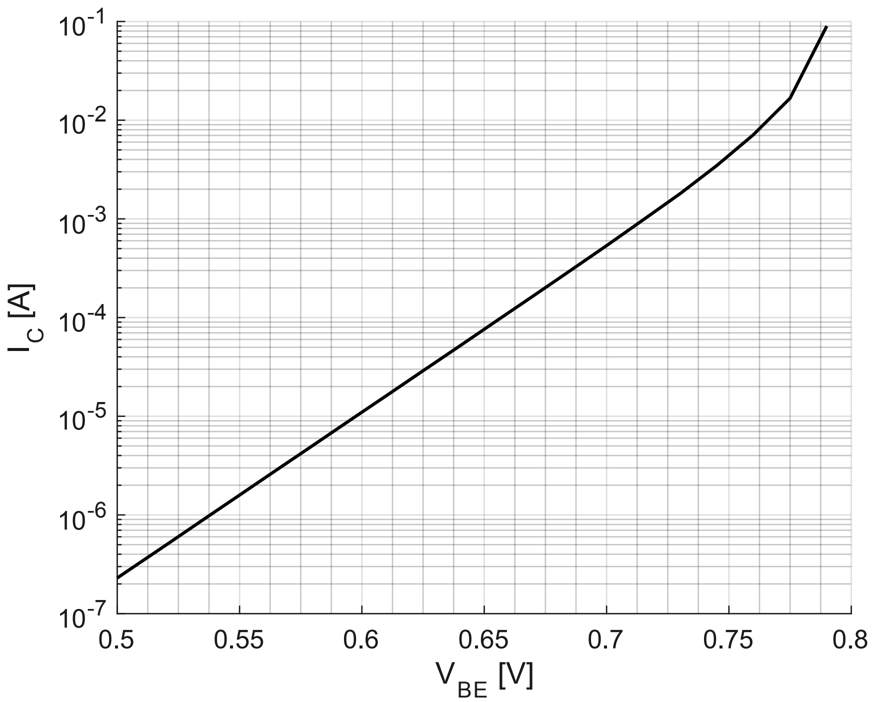


Figure 5 **Collector current I_C= f(V_{BE}), V_{CE} = 8 V**

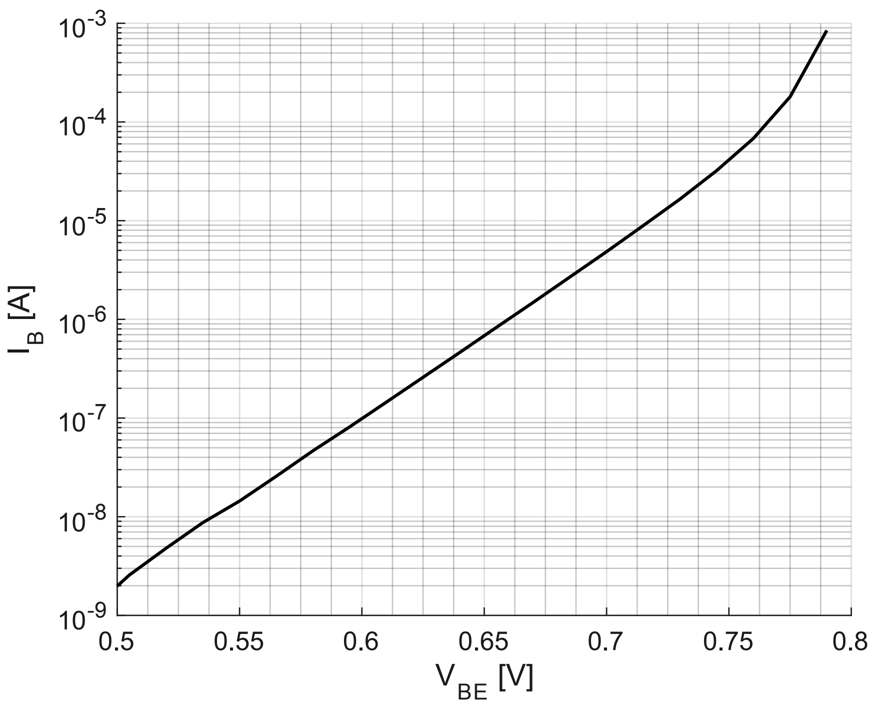


Figure 6 **Base current I_B = f(V_{BE}), V_{CE} = 8 V**

Electrical performance in test fixture

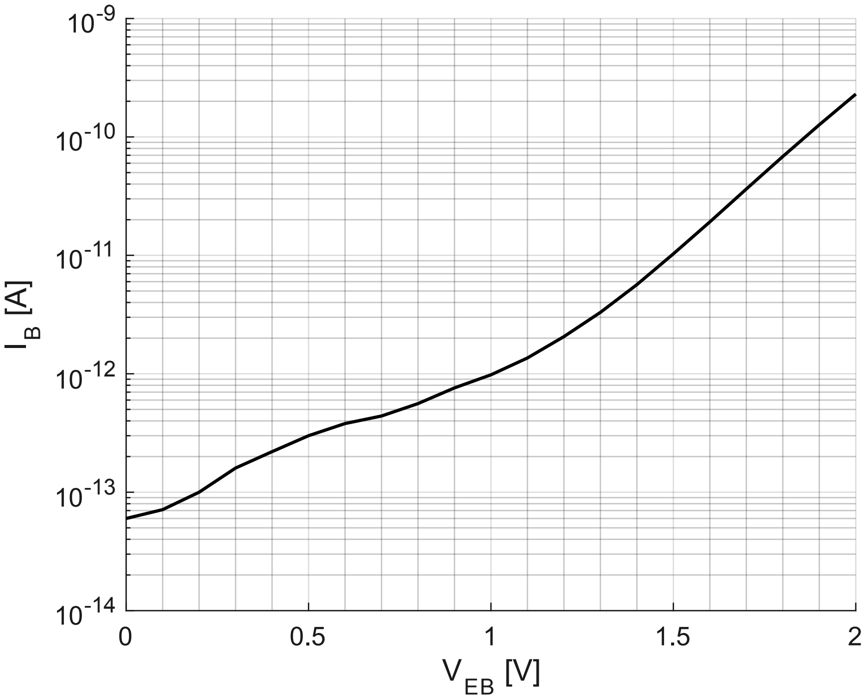


Figure 7 Base/emitter leakage current $I_B = f(V_{EB})$, $V_{CE} = 8$ V

Note: *Regard absolute maximum ratings for I_C, V_{CE} and P_{tot} (see* ***Table 1****)*

3.4 Characteristic AC diagrams

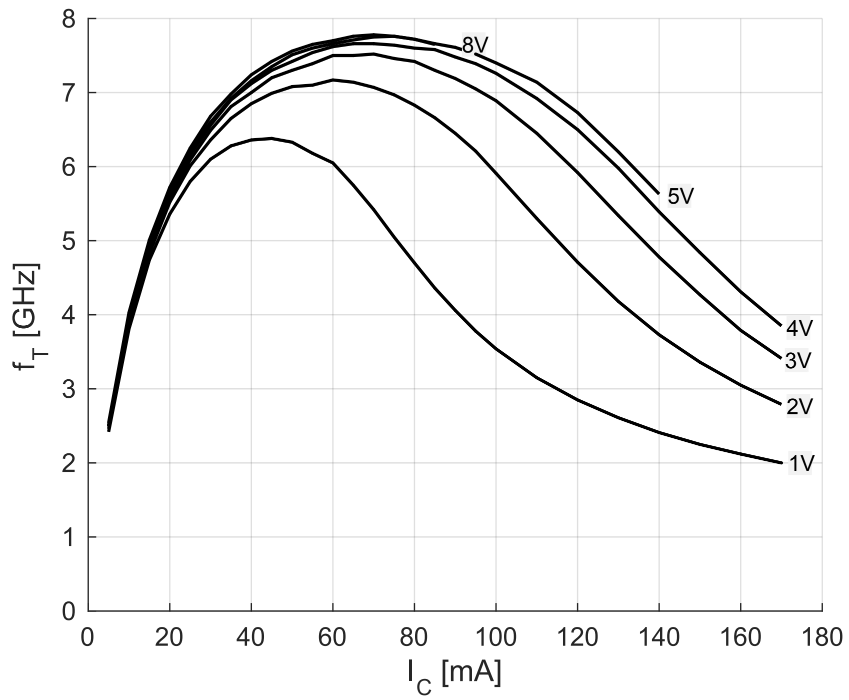


Figure 8 Transition frequency $f_T = f(I_C)$, V_{CE} = parameter

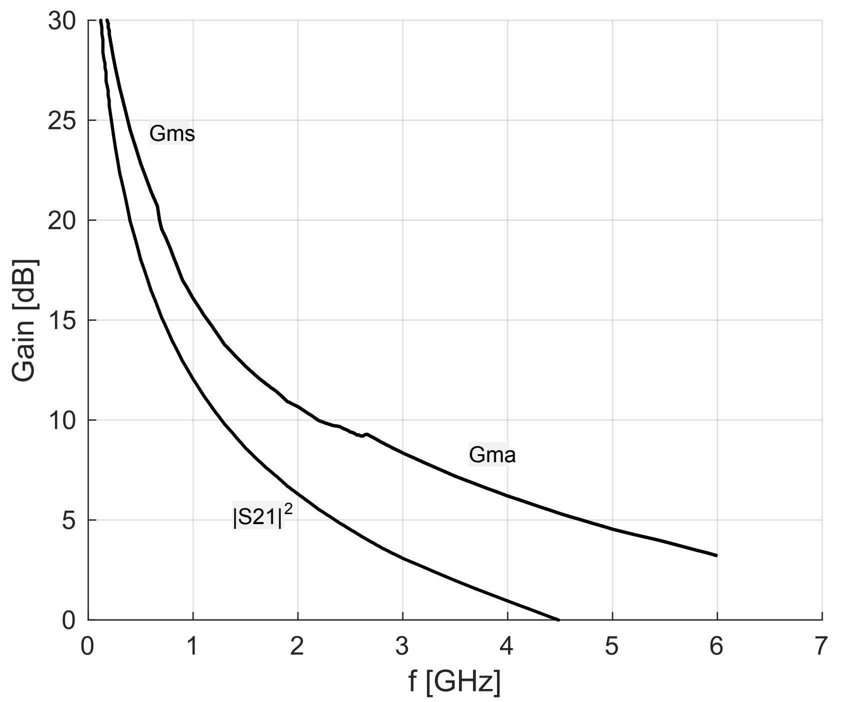


Figure 9 Gain G_{ms}, G_{ma}, $|S_{21}|^2 = f(f)$, I_C = 50 mA, V_{CE} = 8 V

Electrical performance in test fixture

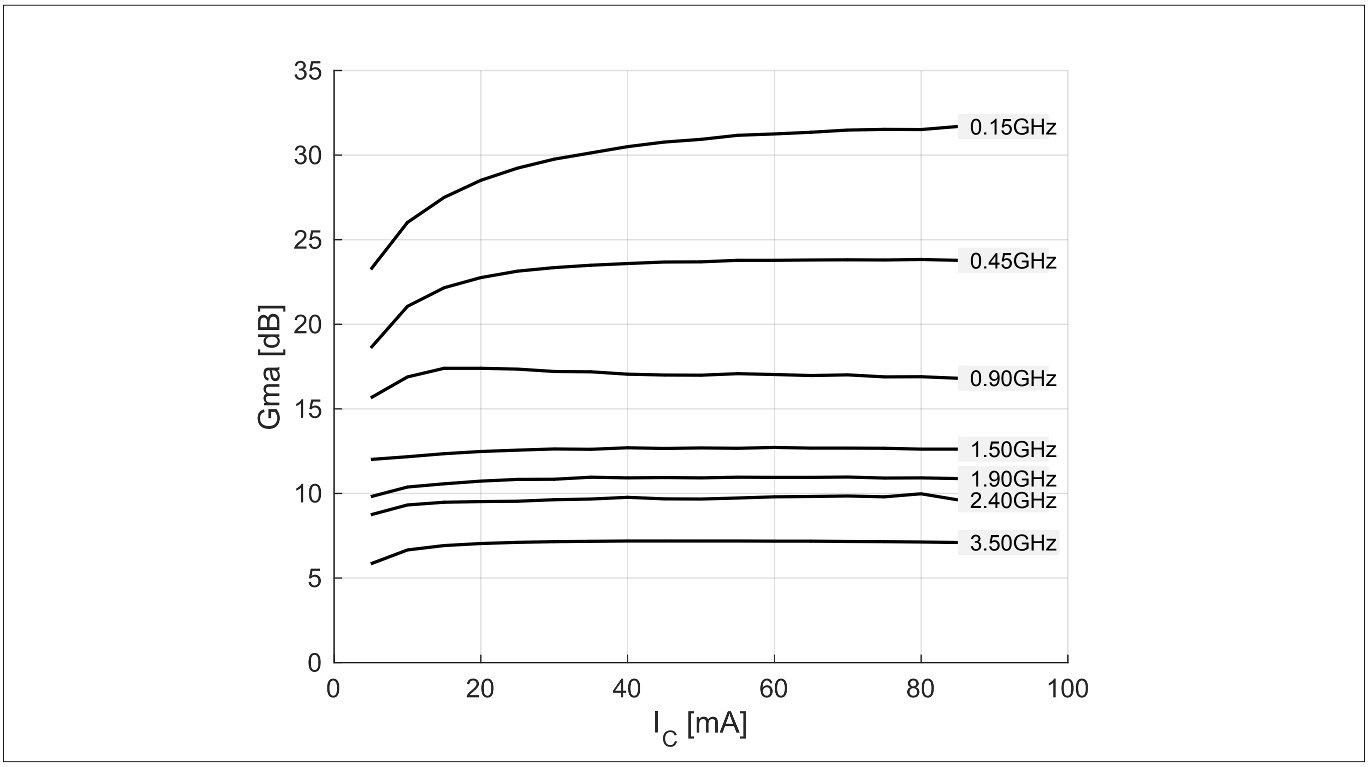


Figure 10 Maximum power gain $G_{max} = f(I_C)$, V_{CE} = 8 V, f = parameter

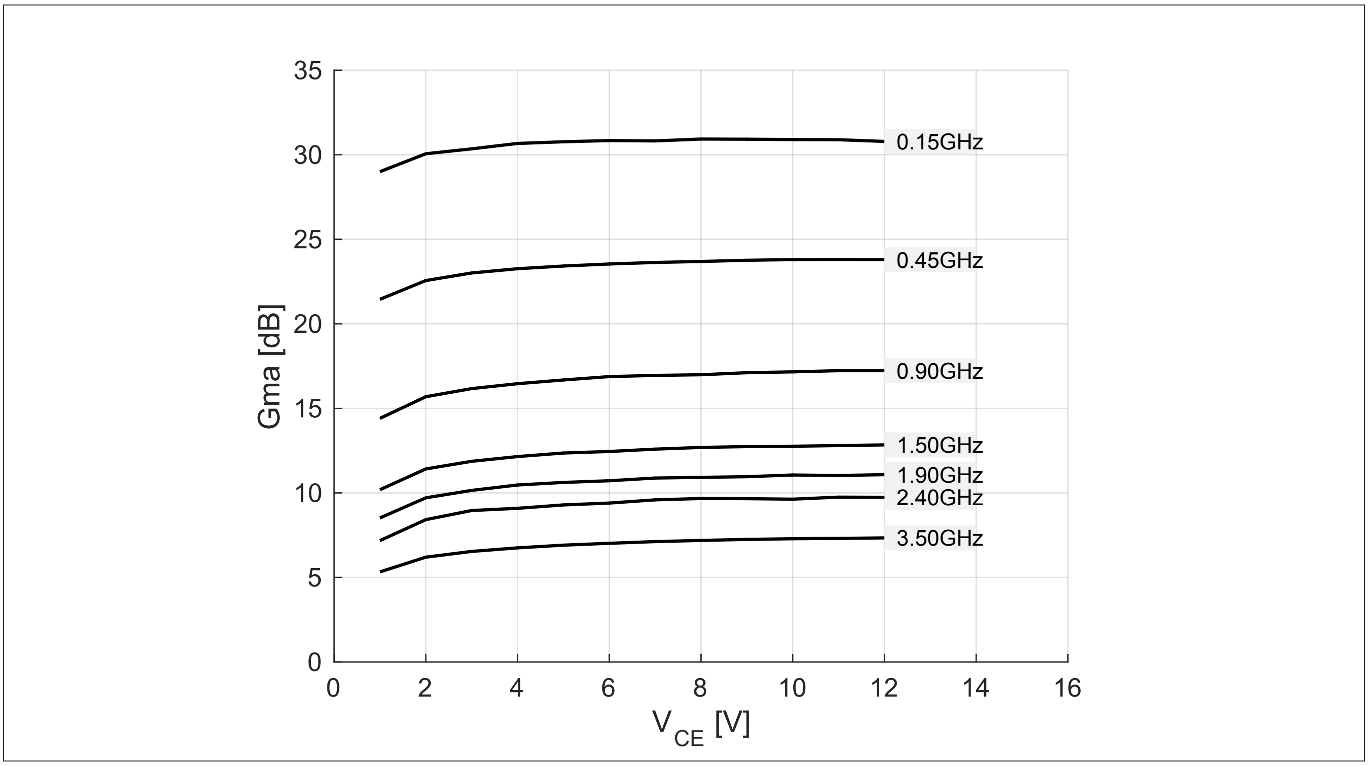


Figure 11 Maximum power gain $G_{max} = f(V_{CE})$, I_C = 50 mA, f = parameter

Electrical performance in test fixture

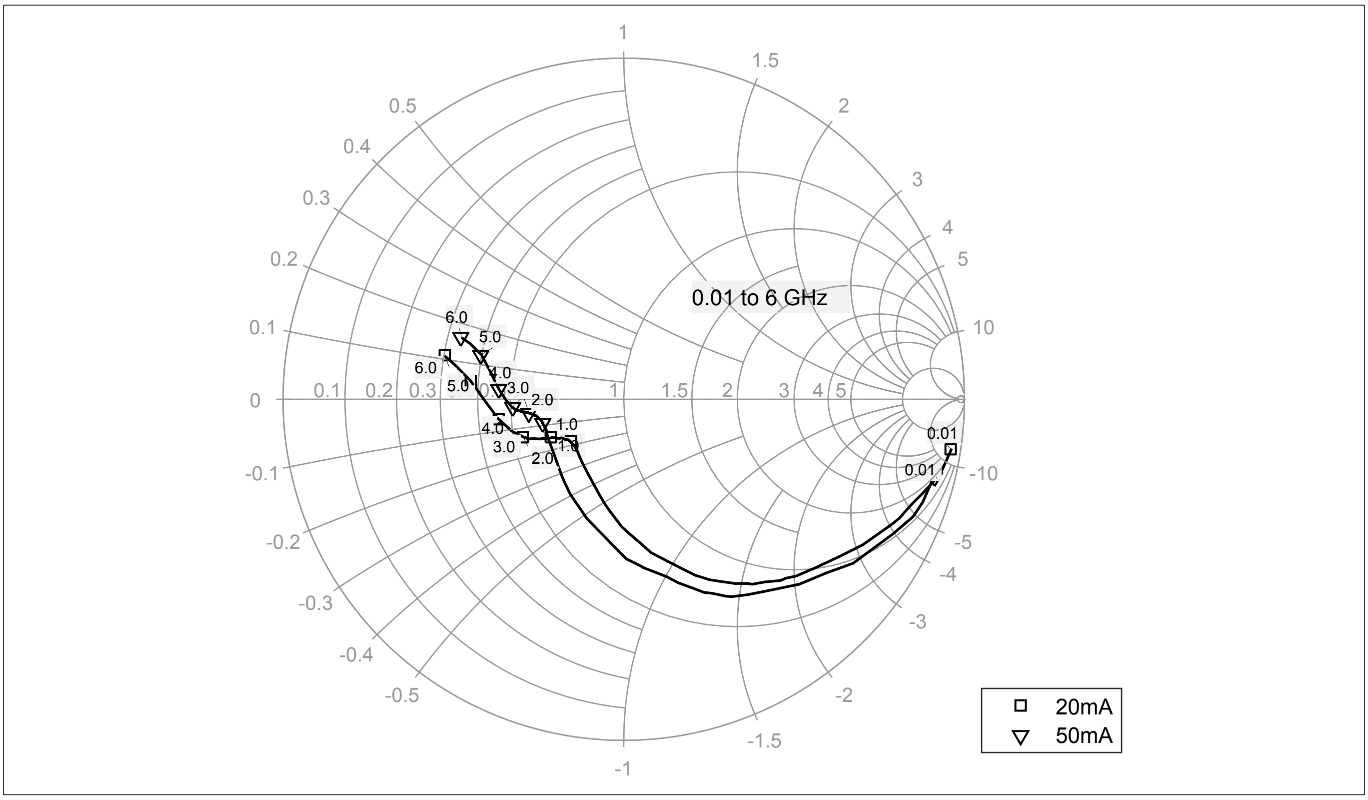


Figure 12 Output reflection coefficient $S_{22} = f(f)$ at $V_{CE} = 8$ V, $I_C = 20, 50$ mA

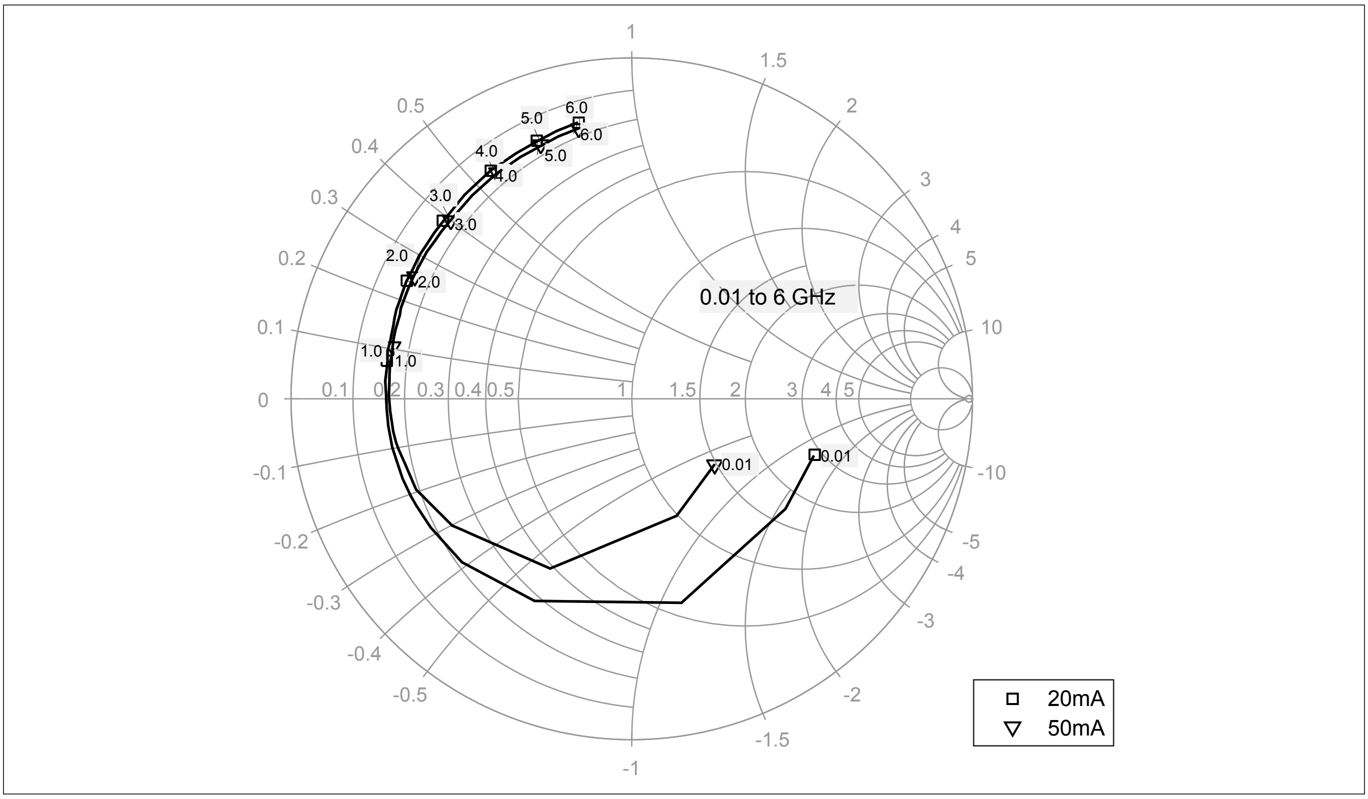


Figure 13 Input reflection coefficient $S_{11} = f(f)$ at $V_{CE} = 8$ V, $I_C = 20, 50$ mA

Electrical performance in test fixture

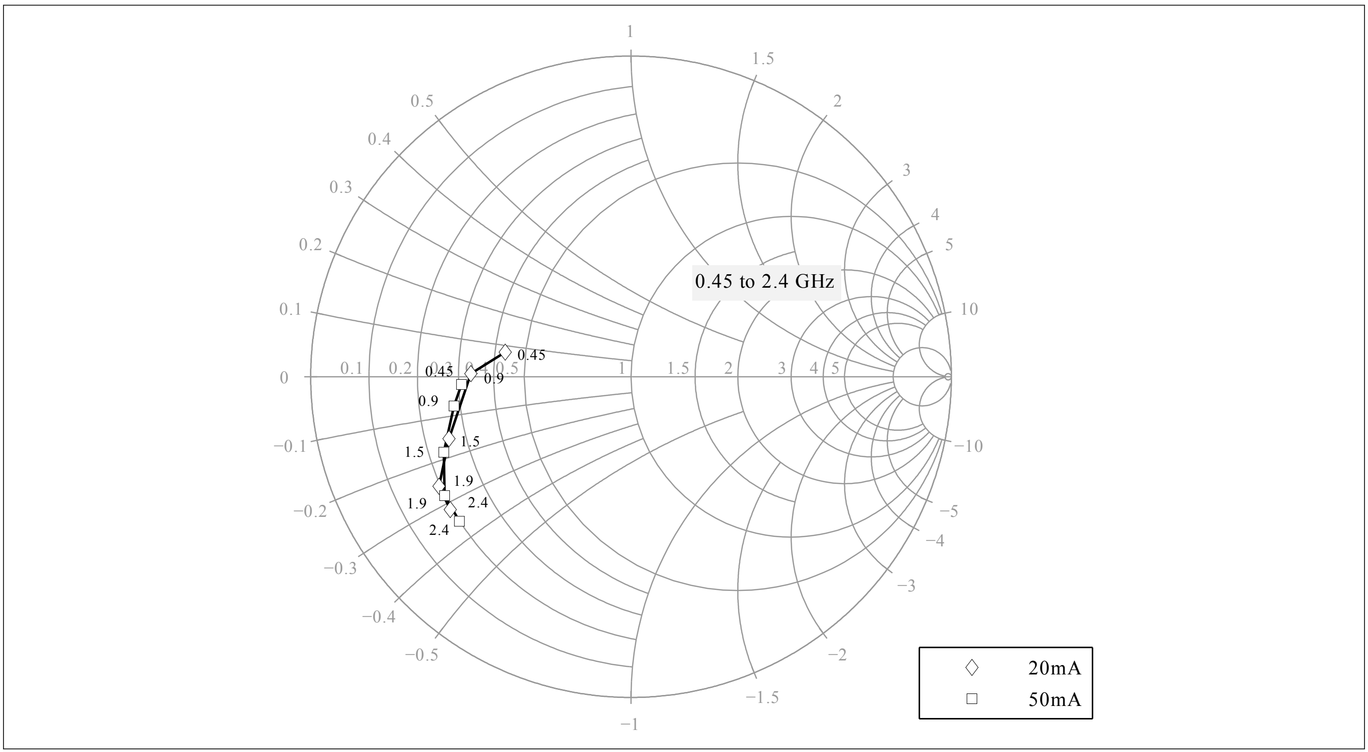


Figure 14 Source impedance for minimum noise figure $Z_{Sopt} = f(f)$, $V_{CE} = 8$ V, $I_C = 20, 50$ mA

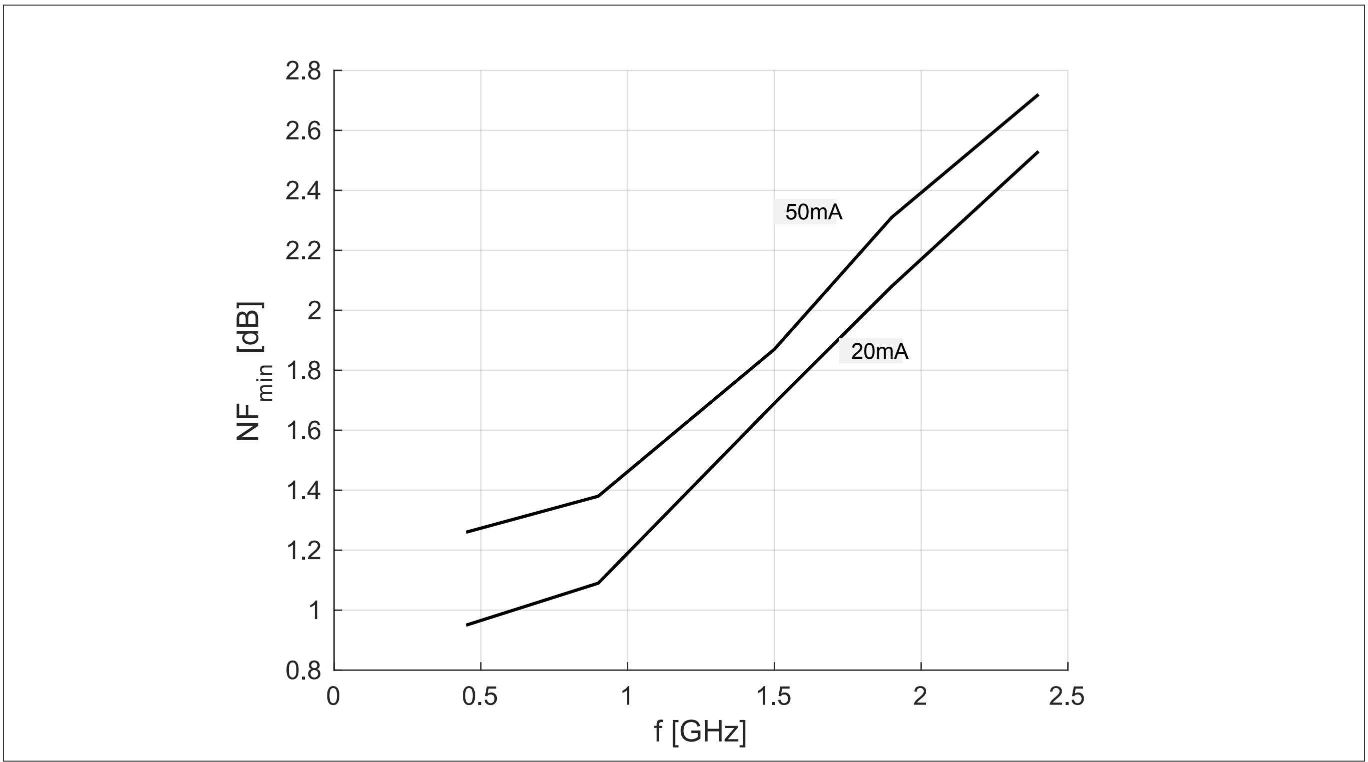


Figure 15 Noise figure $N_{Fmin} = f(f)$, $V_{CE} = 8$ V, $I_C = 20, 50$mA, $Z_S = Z_{Sopt}$

Electrical performance in test fixture

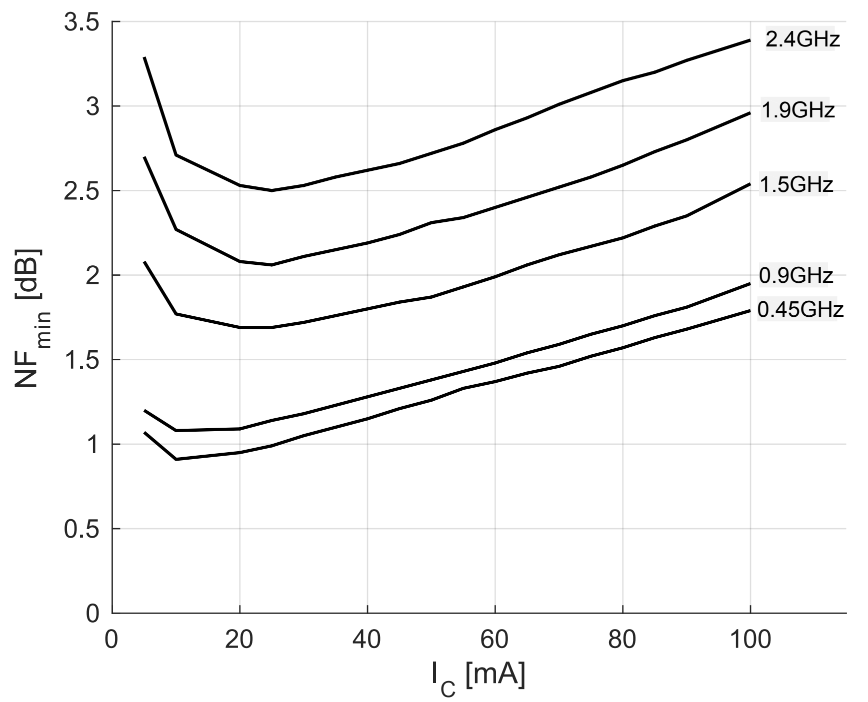


Figure 16 Noise figure $NF_{min} = f(I_C)$, V_{CE} = 8 V, f = parameter, $Z_S = Z_{Sopt}$

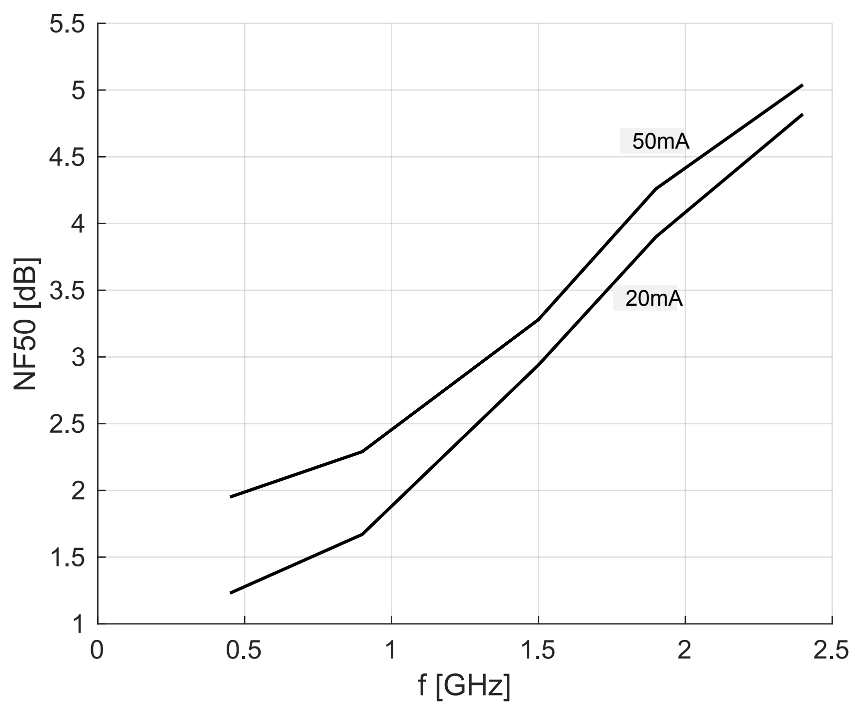


Figure 17 Noise figure $NF_{50} = f(f)$, V_{CE} = 8 V, I_C = 20, 50 mA, Z_S = 50 Ω

Electrical performance in test fixture

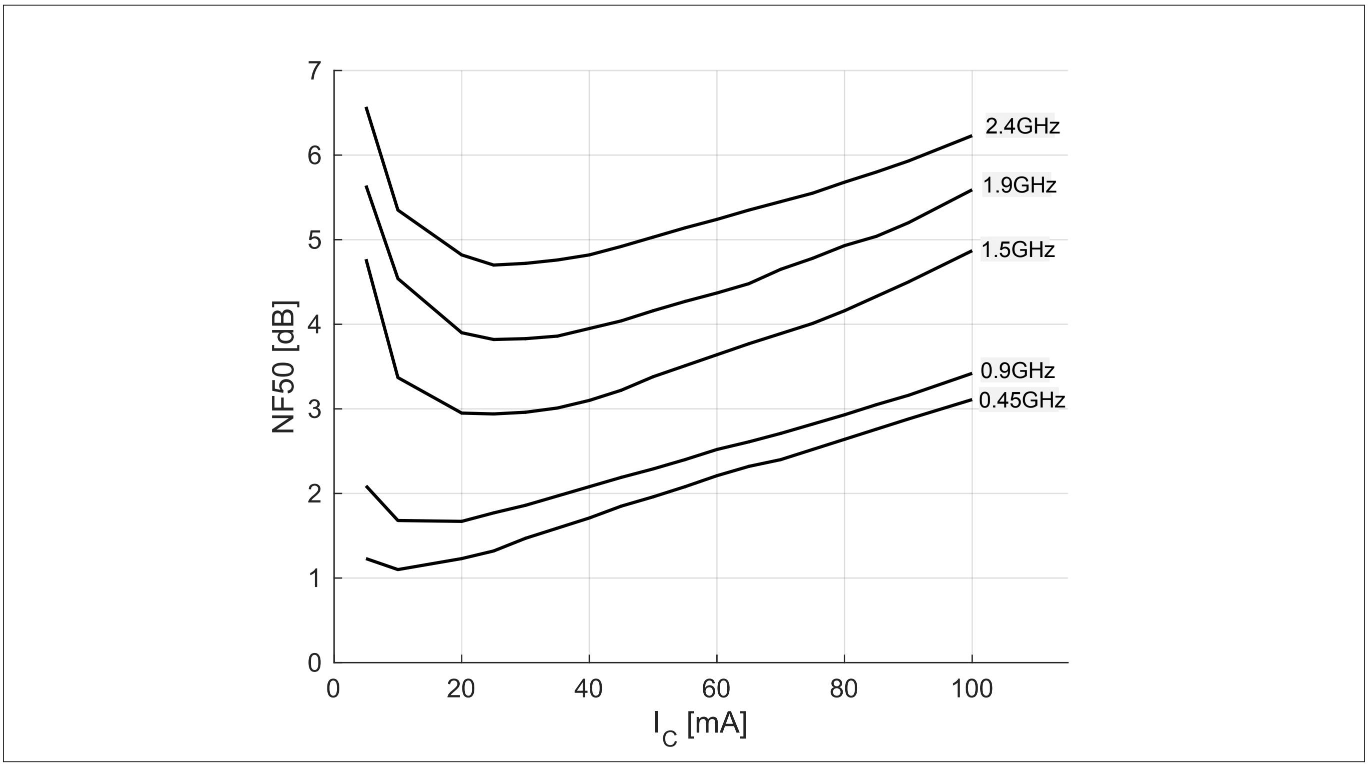


Figure 18 Noise figure $NF_{50} = f(I_C)$, V_{CE} = 8 V, f = parameter, Z_S = 50 Ω

Note: *The curves shown in this chapter* ***Characteristic AC diagrams*** *have been generated using typical devices but shall not be understood as a guarantee that all devices have identical characteristic curves.* T_A *= 25 °C.*

4 SOT343 Package

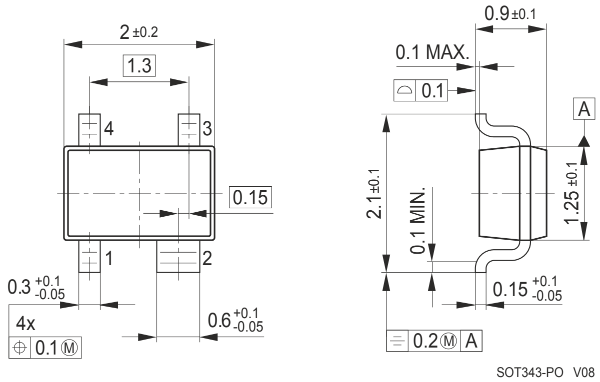


Figure 19 SOT343 package outline (dimension in mm)

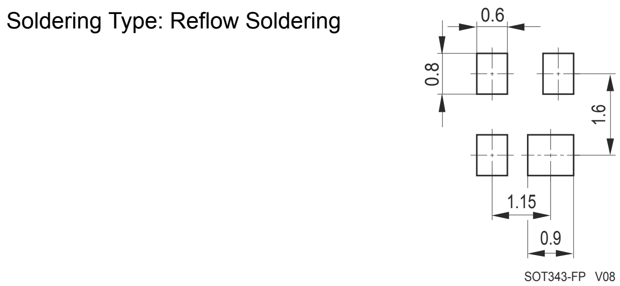


Figure 20 SOT343 footprint (dimension in mm)

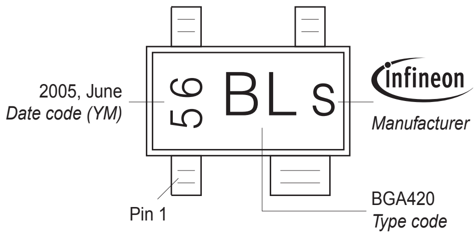


Figure 21 SOT343 marking layout

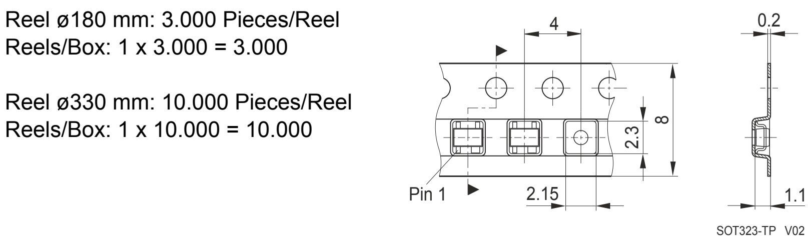


Figure 22 SOT343 standard packing (dimension in mm)

Revision history

Major changes since previous revision

Reference	Description
Revision History: 2016-12-21, Revision 0.9	
rev 0.9	Preliminary datasheet

Trademarks of Infineon Technologies AG

µHVIC™, µIPM™, µPFC™, AU-ConvertIR™, AURIX™, C166™, CanPAK™, CIPOS™, CIPURSE™, CoolDP™, CoolGaN™, COOLiR™, CoolMOS™, CoolSET™, CoolSiC™, DAVE™, DI-POL™, DirectFET™, DrBlade™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPACK™, EconoPIM™, EiceDRIVER™, eupec™, FCOS™, GaNpowIR™, HEXFET™, HITFET™, HybridPACK™, iMOTION™, IRAM™, ISOFACE™, IsoPACK™, LEDrivIR™, LITIX™, MIPAQ™, ModSTACK™, my-d™, NovalithIC™, OPTIGA™, OptiMOS™, ORIGA™, PowIRaudio™, PowIRStage™, PrimePACK™, PrimeSTACK™, PROFET™, PRO-SIL™, RASIC™, REAL3™, SmartLEWIS™, SOLID FLASH™, SPOC™, StrongIRFET™, SupIRBuck™, TEMPFET™, TRENCHSTOP™, TriCore™, UHVIC™, XHP™, XMC™.

Trademarks Update 2015-12-22

Other Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2017-01-20

Published by

Infineon Technologies AG

81726 Munich, Germany

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference
IFX-kst1478698311373

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Bipolar Transistors ***category:***

Click to view products by Infineon ***manufacturer:***

Other Similar products are found below :

MAPRST0912-50 MCH4016-TL-H MMBT5551-G MRF10120 15GN01CA-TB-E PH1214-25M MAPRST0912-350 MMBTH10-TP BFP 640F H6327 BFR 360F H6765 MRF10031 NSVF4009SG4T1G BFP 182R E7764 BFP405H6740XTSA1 MRF10350 ASMA201 BFR360FH6765XTSA1 BFP410H6327XTSA1 BFP620FH7764XTSA1 BFP720ESDH6327XTSA1 BFP720FH6327XTSA1 BFR360L3E6765XTMA1 BFP420H6433XTMA1 BFP420H6740XTSA1 BFP420H6801XTSA1 MCH4015-TL-H BF888H6327XTSA1 MMBT2222A-G BFP196WH6327XTSA1 BFP405FH6327XTSA1 BFP640ESDH6327XTSA1 BFR193L3E6327XTMA1 BFS483H6327XTSA1 NSVF4020SG4T1G NSVF6003SB6T1G MRF10005 BFP420FH6327XTSA1 BFP740FESDH6327XTSA1 BFR181E6327HTSA1 BFR181WH6327XTSA1 BFR182E6327HTSA1 BFR193E6327HTSA1 BFP181E7764HTSA1 BFP183WH6327XTSA1 BFP720H6327XTSA1 BFR182WH6327XTSA1 BFU590GX MAPR-000912-500S00 BFR340FH6327XTSA1 STGWT30HP65FB